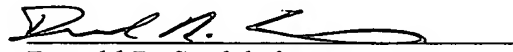


REMARKS

With the filing of the present Reissue application, it is respectfully requested that the foregoing amendments be entered and fully considered by the Examiner. As can be seen from the foregoing amendments, claim 1 of US Patent No. 6,441,420 has been amended to delete reference to "wherein and edge portion of the capacitor upper electrode is formed onto the protective insulating film;" and to delete "direct" when referring to the connection between an impurity diffusion layer serving as a source or drain region of the first field-effect transistor and the edge portion of the capacitor upper electrode. Accordingly, examination on the merits is requested.

It is respectfully submitted that independent claim 1 as well as those claims which depend therefrom distinguish over the prior art of record and are in proper condition for allowance. Should the Examiner believe a conference would be of benefit in expediting the prosecution of the instant application, he is hereby invited to telephone counsel to arrange such a conference.

Respectfully submitted,


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